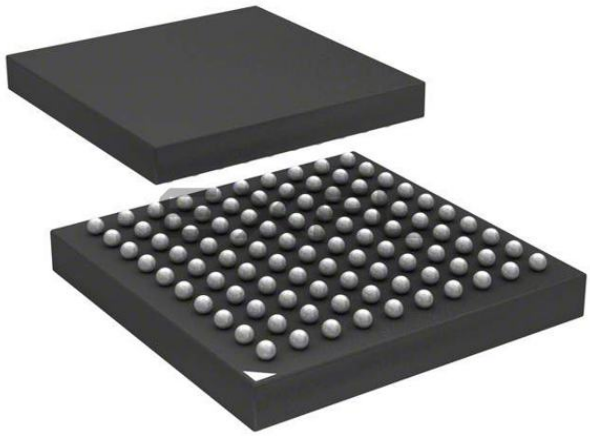


Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

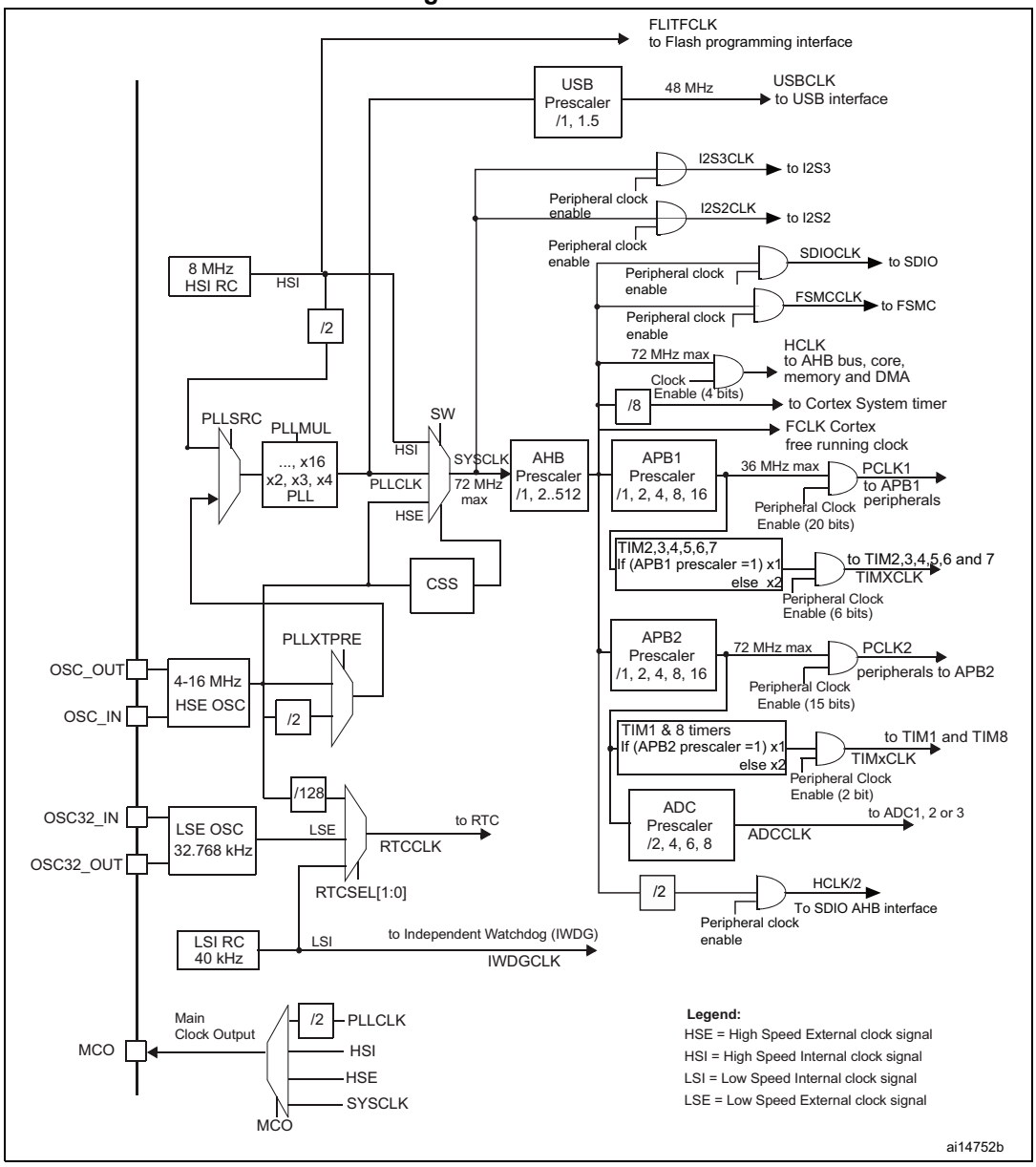
Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, I²C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	DMA, Motor Control PWM, PDR, POR, PVD, PWM, Temp Sensor, WDT
Number of I/O	80
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	64K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LFBGA
Supplier Device Package	100-LFBGA (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f103veh7

Contents

List of tables

Figure 2. Clock tree



1. When the HSI is used as a PLL clock input, the maximum system clock frequency that can be achieved is 64 MHz.
2. For the USB function to be available, both HSE and PLL must be enabled, with the USBCLK at 48 MHz.
3. To have an ADC conversion time of 1 µs, APB2 must be at 14 MHz, 28 MHz or 56 MHz.

2.2 Full compatibility throughout the family

The STM32F103xC/D/E is a complete family whose members are fully pin-to-pin, software and feature compatible. In the reference manual, the STM32F103x4 and STM32F103x6 are identified as low-density devices, the STM32F103x8 and STM32F103xB are referred to as medium-density devices and the STM32F103xC, STM32F103xD and STM32F103xE are referred to as high-density devices.

Low-density and high-density devices are an extension of the STM32F103x8/B medium-density devices, they are specified in the STM32F103x4/6 and STM32F103xC/D/E datasheets, respectively. Low-density devices feature lower Flash memory and RAM capacities, less timers and peripherals. High-density devices have higher Flash memory and RAM capacities, and additional peripherals like SDIO, FSMC, I^2S and DAC while remaining fully compatible with the other members of the family.

The STM32F103x4, STM32F103x6, STM32F103xC, STM32F103xD and STM32F103xE are a drop-in replacement for the STM32F103x8/B devices, allowing the user to try different memory densities and providing a greater degree of freedom during the development cycle.

Moreover, the STM32F103xx performance line family is fully compatible with all existing STM32F101xx access line and STM32F102xx USB access line devices.

Table 3. STM32F103xx family

<table>
<tr><th rowspan="3">Pinout</th><th colspan="2">Low-density devices</th><th colspan="2">Medium-density devices</th><th colspan="3">High-density devices</th></tr>
<tr><th>16 KB Flash</th><th>32 KB Flash(1)</th><th>64 KB Flash</th><th>128 KB Flash</th><th>256 KB Flash</th><th>384 KB Flash</th><th>512 KB Flash</th></tr>
<tr><th>6 KB RAM</th><th>10 KB RAM</th><th>20 KB RAM</th><th>20 KB RAM</th><th>48 RAM</th><th>64 KB RAM</th><th>64 KB RAM</th></tr>
<tr><td>144</td><td colspan="2" rowspan="2"></td><td colspan="2" rowspan="2">3 × USARTs
3 × 16-bit timers
2 × SPIs, 2 × I2Cs, USB, CAN, 1 × PWM timer
2 × ADCs</td><td colspan="3" rowspan="2">5 × USARTs
4 × 16-bit timers, 2 × basic timers
3 × SPIs, 2 × I2Ss, 2 × I2Cs
USB, CAN, 2 × PWM timers
3 × ADCs, 2 × DACs, 1 × SDIO
FSMC (100- and 144-pin packages(2))</td></tr>
<tr><td>100</td></tr>
<tr><td>64</td><td colspan="2" rowspan="3">2 × USARTs
2 × 16-bit timers
1 × SPI, 1 × I2C, USB, CAN, 1 × PWM timer
2 × ADCs</td><td colspan="2" rowspan="2"></td><td colspan="3" rowspan="2"></td></tr>
<tr><td>48</td></tr>
<tr><td>36</td><td colspan="2"></td><td colspan="3"></td></tr>
</table>

1. For orderable part numbers that do not show the A internal code after the temperature range code (6 or 7), the reference datasheet for electrical characteristics is that of the STM32F103x8/B medium-density devices.
2. Ports F and G are not available in devices delivered in 100-pin packages.

Table 5. High-density STM32F103xC/D/E pin definitions

Pins						Pin name	Type(1)	I / O Level(2)	Main function(3) (after reset)	Alternate functions(4)	
LFBGA144	LFBGA100	WLCSP64	LQFP64	LQFP100	LQFP144					Default	Remap
A3	A3	-	-	1	1	PE2	I/O	FT	PE2	TRACECK/ FSMC_A23	-
A2	B3	-	-	2	2	PE3	I/O	FT	PE3	TRACED0/FSMC_A19	-
B2	C3	-	-	3	3	PE4	I/O	FT	PE4	TRACED1/FSMC_A20	-
B3	D3	-	-	4	4	PE5	I/O	FT	PE5	TRACED2/FSMC_A21	-
B4	E3	-	-	5	5	PE6	I/O	FT	PE6	TRACED3/FSMC_A22	-
C2	B2	C6	1	6	6	V_{BAT}	S	-	V_{BAT}	-	-
A1	A2	C8	2	7	7	PC13-TAMPER-RTC(5)	I/O	-	PC13(6)	TAMPER-RTC	-
B1	A1	B8	3	8	8	PC14-OSC32_IN(5)	I/O	-	PC14(6)	OSC32_IN	-
C1	B1	B7	4	9	9	PC15-OSC32_OUT(5)	I/O	-	PC15(6)	OSC32_OUT	-
C3	-	-	-	-	10	PF0	I/O	FT	PF0	FSMC_A0	-
C4	-	-	-	-	11	PF1	I/O	FT	PF1	FSMC_A1	-
D4	-	-	-	-	12	PF2	I/O	FT	PF2	FSMC_A2	-
E2	-	-	-	-	13	PF3	I/O	FT	PF3	FSMC_A3	-
E3	-	-	-	-	14	PF4	I/O	FT	PF4	FSMC_A4	-
E4	-	-	-	-	15	PF5	I/O	FT	PF5	FSMC_A5	-
D2	C2	-	-	10	16	V_{SS_5}	S	-	V_{SS_5}	-	-
D3	D2	-	-	11	17	V_{DD_5}	S	-	V_{DD_5}	-	-
F3	-	-	-	-	18	PF6	I/O	-	PF6	ADC3_IN4/FSMC_NIORD	-
F2	-	-	-	-	19	PF7	I/O	-	PF7	ADC3_IN5/FSMC_NREG	-
G3	-	-	-	-	20	PF8	I/O	-	PF8	ADC3_IN6/FSMC_NIOWR	-
G2	-	-	-	-	21	PF9	I/O	-	PF9	ADC3_IN7/FSMC_CD	-
G1	-	-	-	-	22	PF10	I/O	-	PF10	ADC3_IN8/FSMC_INTR	-
D1	C1	D8	5	12	23	OSC_IN	I	-	OSC_IN	-	-
E1	D1	D7	6	13	24	OSC_OUT	O	-	OSC_OUT	-	-
F1	E1	C7	7	14	25	NRST	I/O	-	NRST	-	-
H1	F1	E8	8	15	26	PC0	I/O	-	PC0	ADC123_IN10	-
H2	F2	F8	9	16	27	PC1	I/O	-	PC1	ADC123_IN11	-

5.3.2 Operating conditions at power-up / power-down

The parameters given in *Table 11* are derived from tests performed under the ambient temperature condition summarized in *Table 10*.

Table 11. Operating conditions at power-up / power-down

Symbol	Parameter	Conditions	Min	Max	Unit
t_{VDD}	V_{DD} rise time rate	-	0	∞	µs/V
	V_{DD} fall time rate		20	∞	

5.3.3 Embedded reset and power control block characteristics

The parameters given in *Table 12* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 10*.

Table 12. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{PVD}	Programmable voltage detector level selection	PLS[2:0]=000 (rising edge)	2.1	2.18	2.26	V
		PLS[2:0]=000 (falling edge)	2	2.08	2.16	
		PLS[2:0]=001 (rising edge)	2.19	2.28	2.37	
		PLS[2:0]=001 (falling edge)	2.09	2.18	2.27	
		PLS[2:0]=010 (rising edge)	2.28	2.38	2.48	
		PLS[2:0]=010 (falling edge)	2.18	2.28	2.38	
		PLS[2:0]=011 (rising edge)	2.38	2.48	2.58	
		PLS[2:0]=011 (falling edge)	2.28	2.38	2.48	
		PLS[2:0]=100 (rising edge)	2.47	2.58	2.69	
		PLS[2:0]=100 (falling edge)	2.37	2.48	2.59	
		PLS[2:0]=101 (rising edge)	2.57	2.68	2.79	
		PLS[2:0]=101 (falling edge)	2.47	2.58	2.69	
		PLS[2:0]=110 (rising edge)	2.66	2.78	2.9	
		PLS[2:0]=110 (falling edge)	2.56	2.68	2.8	
		PLS[2:0]=111 (rising edge)	2.76	2.88	3	
		PLS[2:0]=111 (falling edge)	2.66	2.78	2.9	
$V_{PVDhyst}$(2)	PVD hysteresis	-	-	100	-	mV
$V_{POR/PDR}$	Power on/power down reset threshold	Falling edge	1.8(1)	1.88	1.96	V
		Rising edge	1.84	1.92	2.0	
$V_{PDRhyst}$(2)	PDR hysteresis	-	-	40	-	mV
$T_{RSTTEMPO}$(2)	Reset temporization	-	1	2.5	4.5	ms

1. The product behavior is guaranteed by design down to the minimum $V_{POR/PDR}$ value.
2. Guaranteed by design.

Table 32. Asynchronous non-multiplexed SRAM/PSRAM/NOR write timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FSMC_NE low time	$3t_{HCLK} - 1$	$3t_{HCLK} + 2$	ns
$t_{v(NWE\_NE)}$	FSMC_NEx low to FSMC_NWE low	$t_{HCLK} - 0.5$	$t_{HCLK} + 1.5$	ns
$t_{w(NWE)}$	FSMC_NWE low time	$t_{HCLK} - 0.5$	$t_{HCLK} + 1.5$	ns
$t_{h(NE\_NWE)}$	FSMC_NWE high to FSMC_NE high hold time	t_{HCLK}	-	ns
$t_{v(A\_NE)}$	FSMC_NEx low to FSMC_A valid	-	7.5	ns
$t_{h(A\_NWE)}$	Address hold time after FSMC_NWE high	t_{HCLK}	-	ns
$t_{v(BL\_NE)}$	FSMC_NEx low to FSMC_BL valid	-	0	ns
$t_{h(BL\_NWE)}$	FSMC_BL hold time after FSMC_NWE high	$t_{HCLK} - 0.5$	-	ns
$t_{v(Data\_NE)}$	FSMC_NEx low to Data valid	-	$t_{HCLK} + 7$	ns
$t_{h(Data\_NWE)}$	Data hold time after FSMC_NWE high	t_{HCLK}	-	ns
$t_{v(NADV\_NE)}$	FSMC_NEx low to FSMC_NADV low	-	5.5	ns
$t_{w(NADV)}$	FSMC_NADV low time	-	$t_{HCLK} + 1.5$	ns

1. C_L = 15 pF.
2. Guaranteed by characterization results.

Table 34. Asynchronous multiplexed PSRAM/NOR write timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{h(AD\_NADV)}$	FSMC_AD (address) valid hold time after FSMC_NADV high	$t_{HCLK} - 3$	-	ns
$t_{h(A\_NWE)}$	Address hold time after FSMC_NWE high	$4t_{HCLK}$	-	ns
$t_{v(BL\_NE)}$	FSMC_NEx low to FSMC_BL valid	-	1.6	ns
$t_{h(BL\_NWE)}$	FSMC_BL hold time after FSMC_NWE high	$t_{HCLK} - 1.5$	-	ns
$t_{v(Data\_NADV)}$	FSMC_NADV high to Data valid	-	$t_{HCLK} + 1.5$	ns
$t_{h(Data\_NWE)}$	Data hold time after FSMC_NWE high	$t_{HCLK} - 5$	-	ns

1. C_L = 15 pF.
2. BGuaranteed by characterization results.

Figure 30. Synchronous non-multiplexed NOR/PSRAM read timings

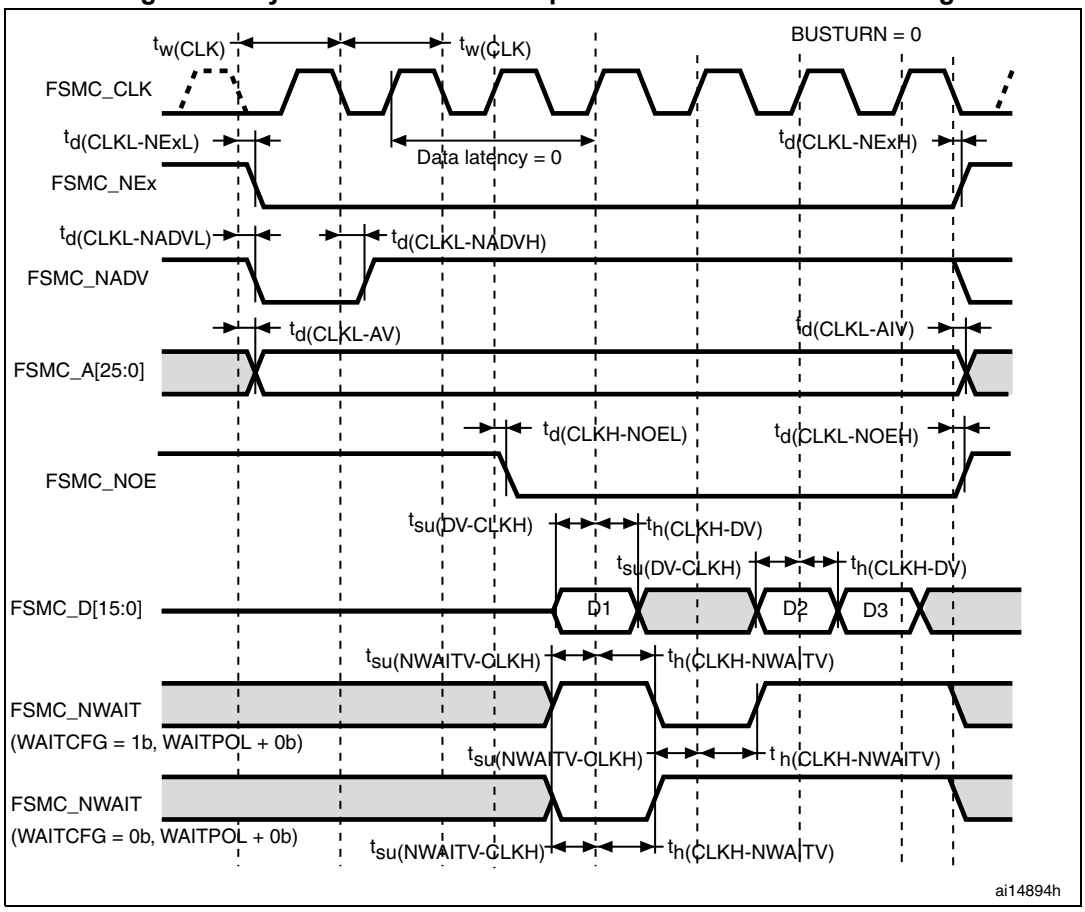


Table 37. Synchronous non-multiplexed NOR/PSRAM read timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(CLK)}$	FSMC_CLK period	27.7	-	ns
$t_{d(CLKL-NExL)}$	FSMC_CLK low to FSMC_NEx low (x = 0...2)	-	1.5	ns
$t_{d(CLKL-NExH)}$	FSMC_CLK low to FSMC_NEx high (x = 0...2)	2	-	ns
$t_{d(CLKL-NADVL)}$	FSMC_CLK low to FSMC_NADV low	-	4	ns
$t_{d(CLKL-NADVH)}$	FSMC_CLK low to FSMC_NADV high	5	-	ns
$t_{d(CLKL-AV)}$	FSMC_CLK low to FSMC_Ax valid (x = 0...25)	-	0	ns
$t_{d(CLKL-AIV)}$	FSMC_CLK low to FSMC_Ax invalid (x = 0...25)	4	-	ns
$t_{d(CLKL-NOEL)}$	FSMC_CLK low to FSMC_NOE low	-	1.5	ns
$t_{d(CLKL-NOEH)}$	FSMC_CLK low to FSMC_NOE high	1.5	-	ns
$t_{su(DV-CLKH)}$	FSMC_D[15:0] valid data before FSMC_CLK high	6.5	-	ns
$t_{h(CLKH-DV)}$	FSMC_D[15:0] valid data after FSMC_CLK high	7	-	ns
$t_{su(NWAITV-CLKH)}$	FSMC_NWAIT valid before FSMC_SMCLK high	7	-	ns
$t_{h(CLKH-NWAITV)}$	FSMC_NWAIT valid after FSMC_CLK high	2	-	ns

1. C_L = 15 pF.
2. Guaranteed by characterization results.

I^2S - SPI characteristics

Unless otherwise specified, the parameters given in *Table 53* for SPI or in *Table 54* for I^2S are derived from tests performed under ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in *Table 10*.

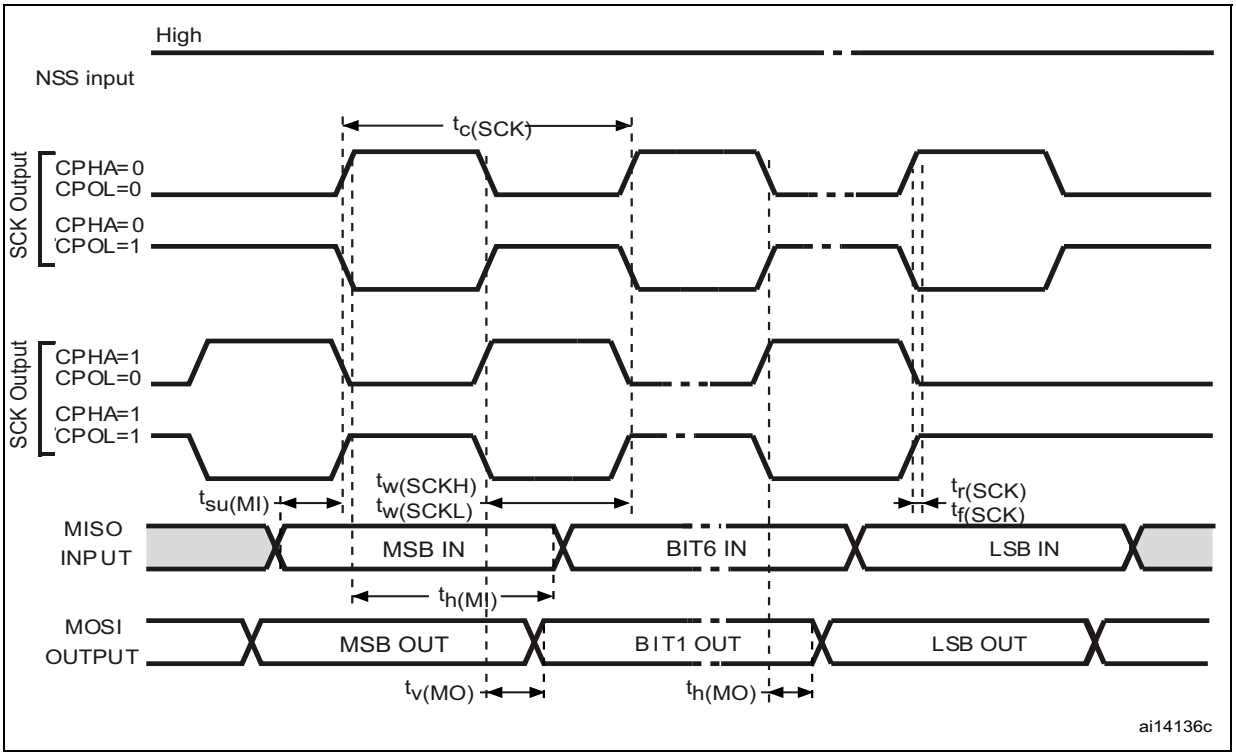
Refer to *Section 5.3.14: I/O port characteristics* for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO for SPI and WS, CK, SD for I^2S).

Table 53. SPI characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
f_{SCK} $1/t_{c(SCK)}$	SPI clock frequency	Master mode	-	18	MHz
		Slave mode	-	18	
$t_{r(SCK)}$ $t_{f(SCK)}$	SPI clock rise and fall time	Capacitive load: C = 30 pF	-	8	ns
DuCy(SCK)	SPI slave input clock duty cycle	Slave mode	30	70	%
$t_{su(NSS)}$ (1)	NSS setup time	Slave mode	$4t_{PCLK}$	-	ns
$t_{h(NSS)}$ (1)	NSS hold time	Slave mode	$2t_{PCLK}$	-	
$t_{w(SCKH)}$ (1) $t_{w(SCKL)}$ (1)	SCK high and low time	Master mode, f_{PCLK} = 36 MHz, presc = 4	50	60	
$t_{su(MI)}$ (1) $t_{su(SI)}$ (1)	Data input setup time	Master mode	5	-	
		Slave mode	5	-	
$t_{h(MI)}$ (1)	Data input hold time	Master mode	5	-	
$t_{h(SI)}$ (1)		Slave mode	4	-	
$t_{a(SO)}$ (1)(2)	Data output access time	Slave mode, f_{PCLK} = 20 MHz	0	$3t_{PCLK}$	
$t_{dis(SO)}$ (1)(3)	Data output disable time	Slave mode	2	10	
$t_{v(SO)}$ (1)	Data output valid time	Slave mode (after enable edge)	-	25	
$t_{v(MO)}$ (1)	Data output valid time	Master mode (after enable edge)	-	5	
$t_{h(SO)}$ (1)	Data output hold time	Slave mode (after enable edge)	15	-	
$t_{h(MO)}$ (1)		Master mode (after enable edge)	2	-	

1. Guaranteed by characterization results.
2. Min time is for the minimum time to drive the output and the max time is for the maximum time to validate the data.
3. Min time is for the minimum time to invalidate the output and the max time is for the maximum time to put the data in Hi-Z

Figure 51. SPI timing diagram - master mode(1)



1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

Table 57. USB DC electrical characteristics

Symbol	Parameter	Conditions	Min.(1)	Max.(1)	Unit
Input levels					
V_{DD}	USB operating voltage(2)	-	3.0(3)	3.6	V
V_{DI}(4)	Differential input sensitivity	I(USB_DP, USB_DM)	0.2	-	V
V_{CM}(4)	Differential common mode range	Includes V_{DI} range	0.8	2.5	
V_{SE}(4)	Single ended receiver threshold	-	1.3	2.0	
Output levels					
V_{OL}	Static output level low	R_L of 1.5 kΩ to 3.6 V(5)	-	0.3	V
V_{OH}	Static output level high	R_L of 15 kΩ to V_{SS}(5)	2.8	3.6	

1. All the voltages are measured from the local ground potential.
2. To be compliant with the USB 2.0 full-speed electrical specification, the USB_DP (D+) pin should be pulled up with a 1.5 kΩ resistor to a 3.0-to-3.6 V voltage range.
3. The STM32F103xC/D/E USB functionality is ensured down to 2.7 V but not the full USB electrical characteristics which are degraded in the 2.7-to-3.0 V V_{DD} voltage range.
4. Guaranteed by characterization results.
5. R_L is the load connected on the USB drivers

Figure 56. USB timings: definition of data signal rise and fall time

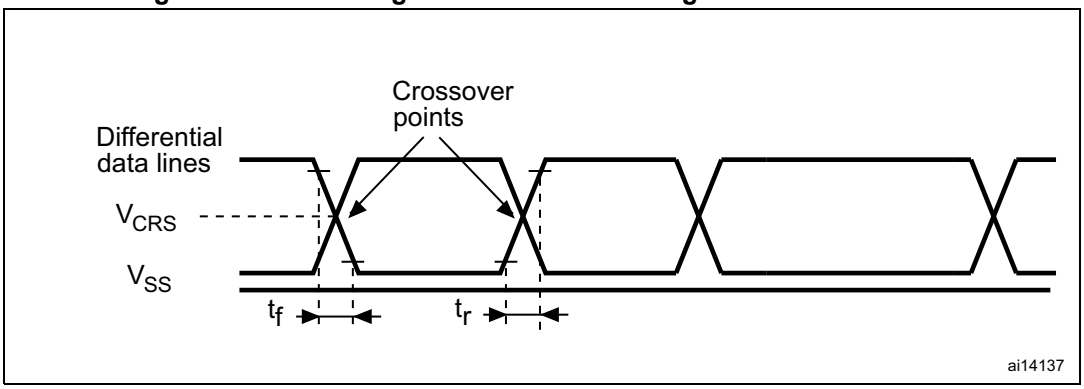
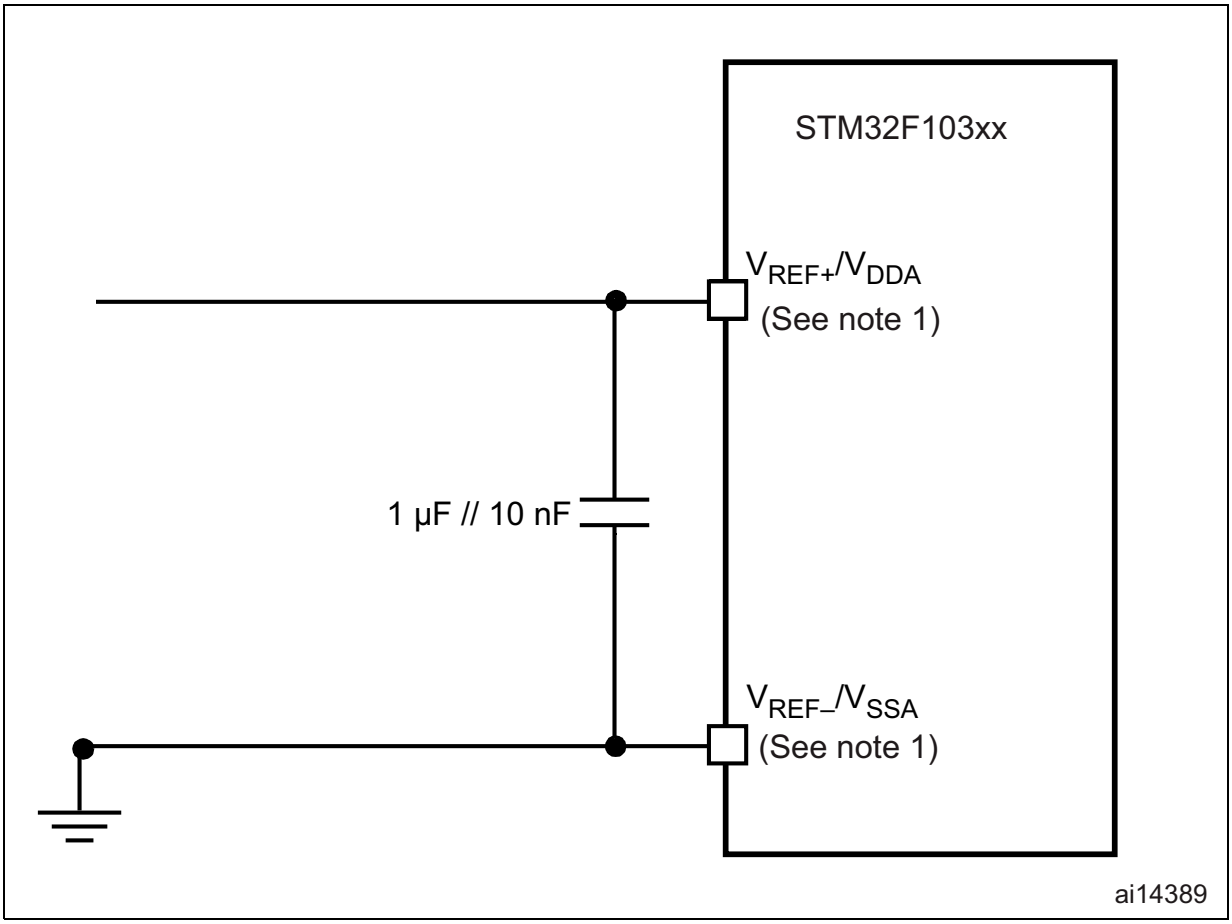


Table 58. USB: full-speed electrical characteristics

Driver characteristics(1)					
Symbol	**Parameter**	**Conditions**	**Min**	**Max**	**Unit**
t_r	Rise time(2)	C_L = 50 pF	4	20	ns
t_f	Fall Time(2)	C_L = 50 pF	4	20	ns
t_{rfm}	Rise/ fall time matching	t_r/t_f	90	110	%
V_{CRS}	Output signal crossover voltage	-	1.3	2.0	V

1. Guaranteed by design.
2. Measured from 10% to 90% of the data signal. For more detailed informations, please refer to USB Specification - Chapter 7 (version 2.0).

Figure 60. Power supply and reference decoupling (V_{REF+} connected to V_{DDA})



1. V_{REF+} and $V_{REF–}$ inputs are available only on 100-pin packages.

Table 65. LFBGA144 – 144-ball low profile fine pitch ball grid array, 10 x 10 mm, 0.8 mm pitch, package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Typ	Min	Max
b	0.350	0.400	0.450	0.0138	0.0157	0.0177
D	9.900	10.000	10.100	0.3898	0.3937	0.3976
D1	-	8.800	-	-	0.3465	-
E	9.900	10.000	10.100	0.3898	0.3937	0.3976
E1	-	8.800	-	-	0.3465	-
e	-	0.800	-	-	0.0315	-
F	-	0.600	-	-	0.0236	-
ddd	-	-	0.100	-	-	0.0039
eee	-	-	0.150	-	-	0.0059
fff	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.
2. STATSChipPAC package dimensions.

Figure 63. LFBGA144 – 144-ball low profile fine pitch ball grid array, 10 x 10 mm, 0.8 mm pitch, package recommended footprint

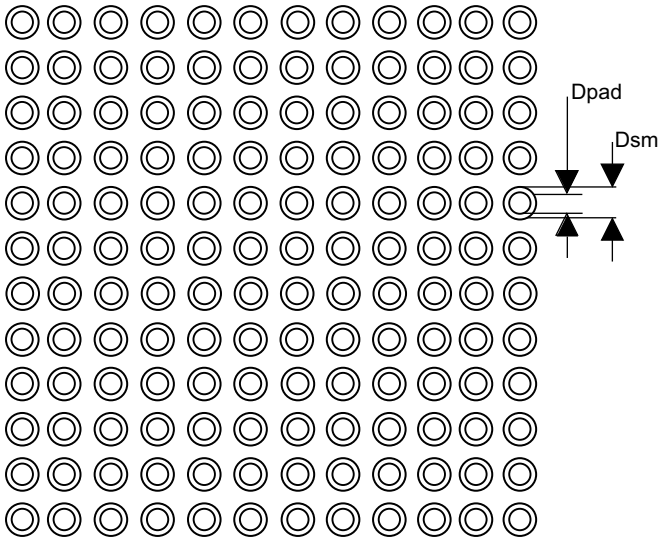
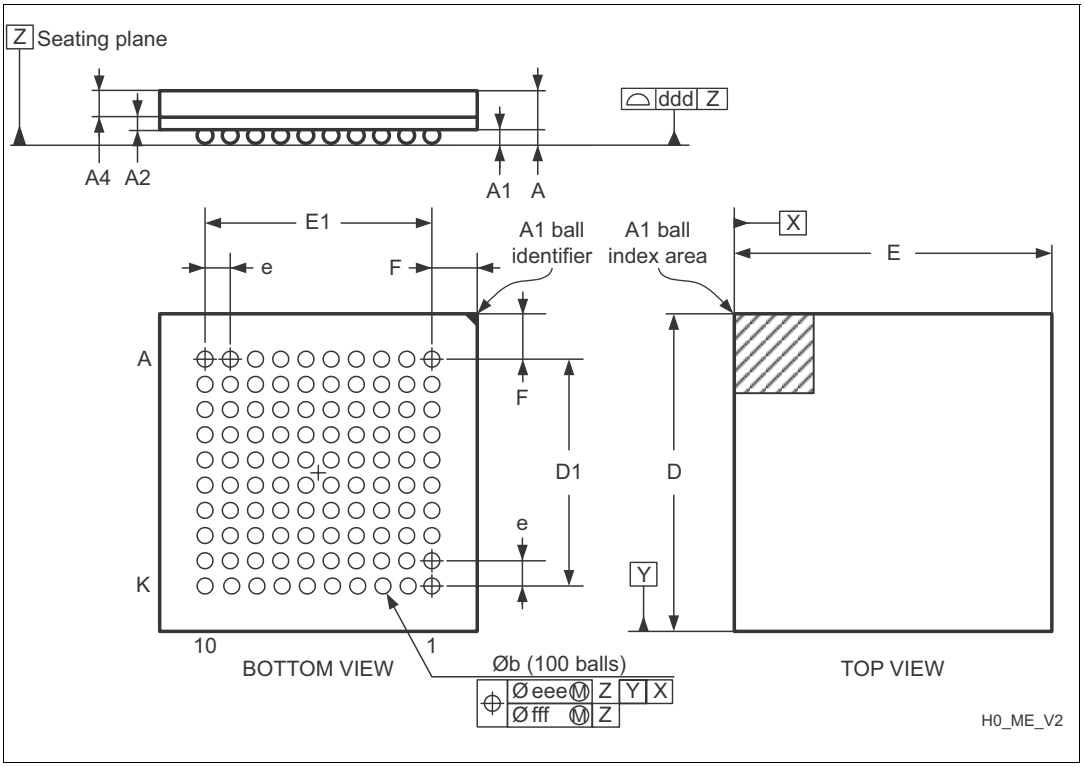


Table 66. LFBGA144 recommended PCB design rules (0.8 mm pitch BGA)

Dimension	Recommended values
Pitch	0.8 mm
Dpad	0.400 mm
UBM	0.350 mm

6.2 LFBGA100 package information

Figure 65. LFBGA100 - 10 x 10 mm low profile fine pitch ball grid array package outline



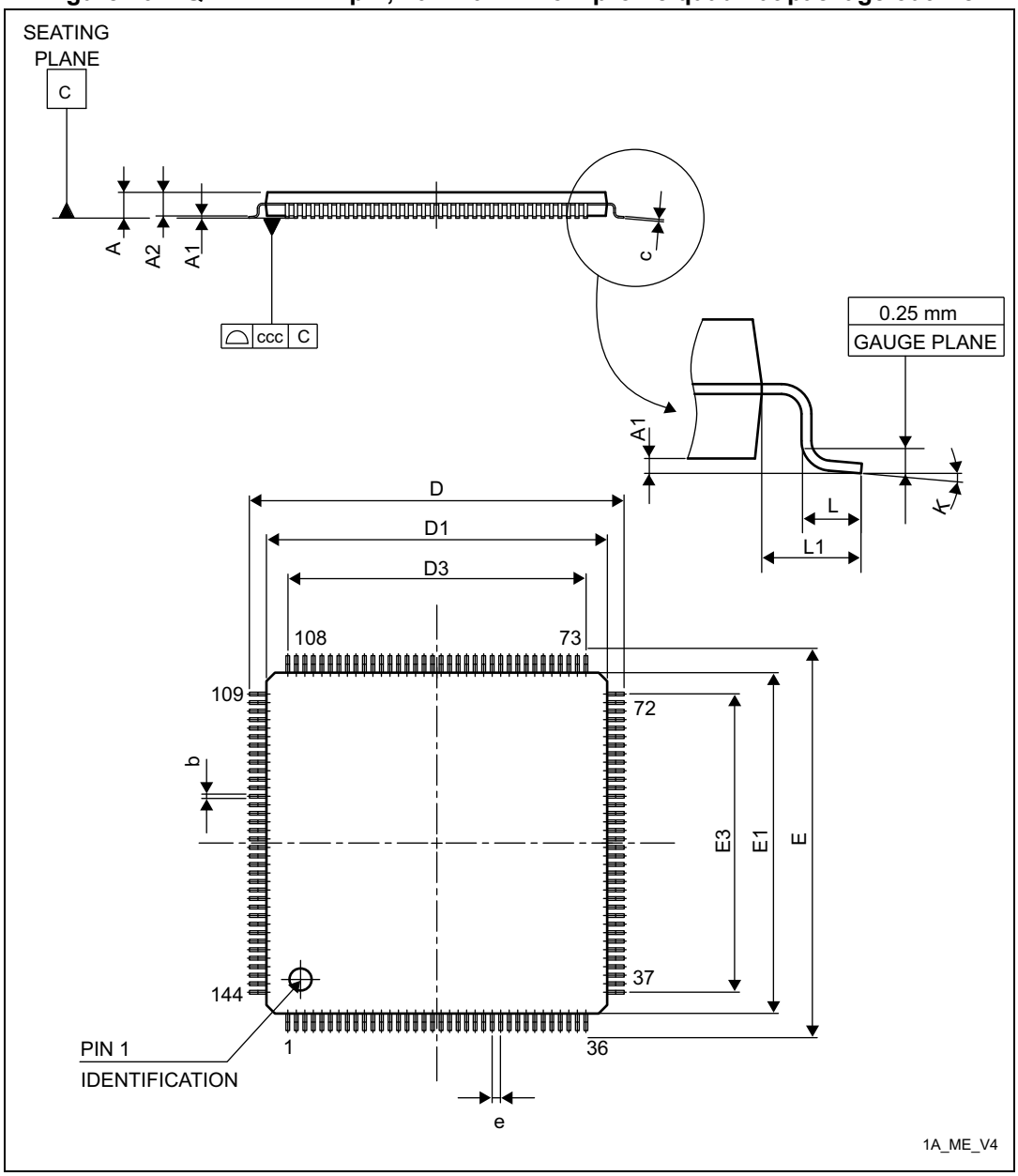
1. Drawing is not to scale.

Table 67. LFBGA100 - 10 x 10 mm low profile fine pitch ball grid array package mechanical data

Symbol	millimeters			inches(1)		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.700	-	-	0.0669
A1	0.270	-	-	0.0106	-	-
A2	-	0.300	-	-	0.0118	-
A4	-	-	0.800	-	-	0.0315
b	0.450	0.500	0.550	0.0177	0.0197	0.0217
D	9.850	10.000	10.150	0.3878	0.3937	0.3996
D1	-	7.200	-	-	0.2835	-
E	9.850	10.000	10.150	0.3878	0.3937	0.3996
E1	-	7.200	-	-	0.2835	-
e	-	0.800	-	-	0.0315	-
F	-	1.400	-	-	0.0551	-
ddd	-	-	0.120	-	-	0.0047

6.4 LQFP144 package information

Figure 70. LQFP144 - 144-pin, 20 x 20 mm low-profile quad flat package outline



1. Drawing is not to scale.

Table 71. LQFP144 - 144-pin, 20 x 20 mm low-profile quad flat package mechanical data

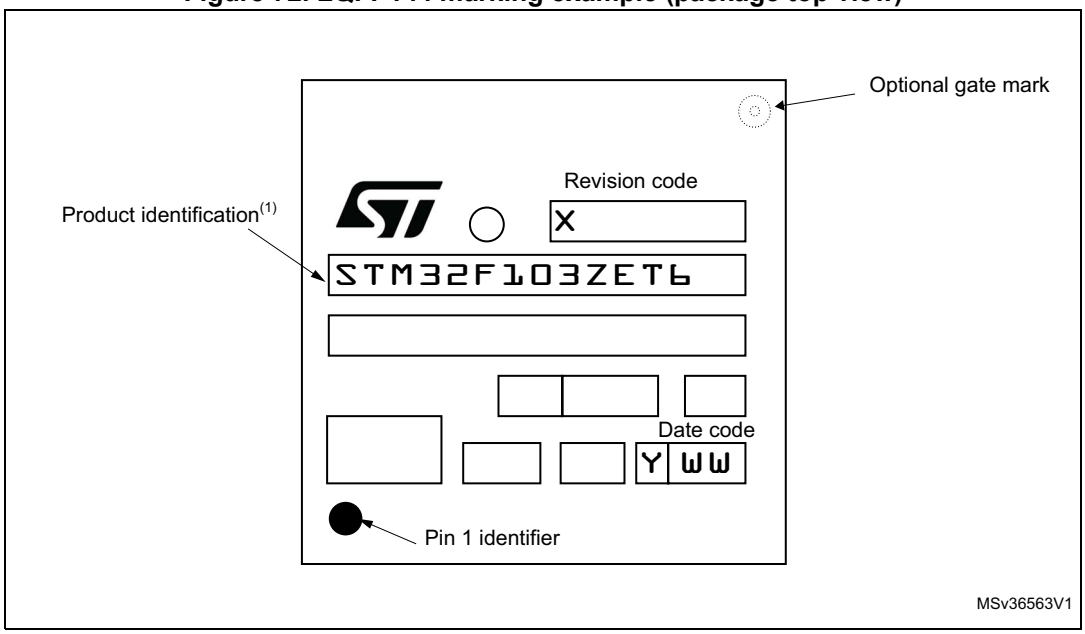
Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	21.800	22.000	22.200	0.8583	0.8661	0.8740
D1	19.800	20.000	20.200	0.7795	0.7874	0.7953
D3	-	17.500	-	-	0.6890	-
E	21.800	22.000	22.200	0.8583	0.8661	0.8740
E1	19.800	20.000	20.200	0.7795	0.7874	0.7953
E3	-	17.500	-	-	0.6890	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	3.5°	7°	0°	3.5°	7°
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Device marking for LQFP144 package

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Figure 72. LQFP144 marking example (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

Table 76.Document revision history

Date	Revision	Changes
21-Jul-2009	6	*Figure 1: STM32F103xC, STM32F103xD and STM32F103xE performance line block diagram* updated. *Note 5* updated and *Note 4* added in *Table 5: High-density STM32F103xC/D/E pin definitions*. V_{RERINT} and T_{Coeff} added to *Table 13: Embedded internal reference voltage*. *Table 16: Maximum current consumption in Sleep mode, code running from Flash or RAM* modified. f_{HSE_ext} min modified in *Table 21: High-speed external user clock characteristics*. C_{L1} and C_{L2} replaced by C in *Table 23: HSE 4-16 MHz oscillator characteristics* and *Table 24: LSE oscillator characteristics (fLSE = 32.768 kHz)*, notes modified and moved below the tables. *Note 1* modified below *Figure 29: Synchronous multiplexed PSRAM write timings*. *Table 25: HSI oscillator characteristics* modified. Conditions removed from *Table 27: Low-power mode wakeup timings*. Jitter added to *Table 28: PLL characteristics*. *Figure 47: Recommended NRST pin protection* modified. In *Table 31: Asynchronous non-multiplexed SRAM/PSRAM/NOR read timings*: $t_{h(BL\_NOE)}$ and $t_{h(A\_NOE)}$ modified. In *Table 32: Asynchronous non-multiplexed SRAM/PSRAM/NOR write timings*: $t_{h(A\_NWE)}$ and $t_{h(Data\_NWE)}$ modified. In *Table 33: Asynchronous multiplexed PSRAM/NOR read timings*: $t_{h(AD\_NADV)}$ and $t_{h(A\_NOE)}$ modified. In *Table 34: Asynchronous multiplexed PSRAM/NOR write timings*: $t_{h(A\_NWE)}$ modified. In *Table 35: Synchronous multiplexed NOR/PSRAM read timings*: $t_{h(CLKH-NWAITV)}$ modified. In *Table 40: Switching characteristics for NAND Flash read and write cycles*: $t_{h(NOE-D)}$ modified. *Table 53: SPI characteristics* modified. Values added to *Table 54: I2S characteristics* and *Table 55: SD / MMC characteristics*. C_{ADC} and R_{AIN} parameters modified in *Table 59: ADC characteristics*. R_{AIN} max values modified in *Table 60: RAIN max for fADC = 14 MHz*. *Table 71: DAC characteristics* modified. *Figure 61: 12-bit buffered /non-buffered DAC* added. *Figure 63: LFBGA100 - 10 x 10 mm low profile fine pitch ball grid array package outline* and *Table 75: LFBGA100 - 10 x 10 mm low profile fine pitch ball grid array package mechanical data* updated.
24-Sep-2009	7	Number of DACs corrected in *Table 3: STM32F103xx family*. I_{DD_VBAT} updated in *Table 17: Typical and maximum current consumptions in Stop and Standby modes*. *Figure 16: Typical current consumption on VBAT with RTC on vs. temperature at different VBAT values* added. IEC 1000 standard updated to IEC 61000 and SAE J1752/3 updated to IEC 61967-2 in *Section 5.3.11: EMC characteristics on page 87*. *Table 63: DAC characteristics* modified. Small text changes.